



Product Overview

MBRAF2H100: 2.0 A, 100 V Schottky Rectifier

For complete documentation, see the [data sheet](#)

Product Description

This device employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system.

Features

- Low Profile Package for Space Constrained Applications
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- 150°C Operating Junction Temperature
- Guard-Ring for Stress Protection
- These are Pb-Free and Halide-Free Devices

Mechanical Characteristics:

- Case: Epoxy, Molded, Epoxy Meets UL 94, V-0
- Weight: 95 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

Part Electrical Specifications

Product	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (uA)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_{rr} Max (ns)	C_j Max (pF)	Package Type
MBRAF2H100T3G	AEC Qualified Pb-free Halide free	Active	Single	100	0.79	8	2	130	-	-	SMA-FL

For more information please contact your local sales support at www.onsemi.com

Created on: 7/11/2015